



Silicon Power Schottky Diode

Features

- High Surge Capability
- Types up to 100 V V_{RRM}

MBR20045CT thru MBR200100CTR

$$V_{RRM} = 20 \text{ V} - 100 \text{ V}$$

$$I_F = 200 \text{ A}$$

Twin Tower Package



Maximum ratings, at $T_J = 25 \text{ }^\circ\text{C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBR20045CT (R)	MBR20060CT (R)	MBR20080CT (R)	MBR200100CT (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		45	60	80	100	V
RMS reverse voltage	V_{RMS}		32	42	56	70	V
DC blocking voltage	V_{DC}		45	60	80	100	V
Continuous forward current	I_F	$T_C \leq 136 \text{ }^\circ\text{C}$	200	200	200	200	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25 \text{ }^\circ\text{C}$, $t_p = 8.3 \text{ ms}$	1500	1500	1500	1500	A
Operating temperature	T_J		-40 to 175	-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$
Storage temperature	T_{stg}		-40 to 175	-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$

Electrical characteristics, at $T_J = 25 \text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	MBR20045CT (R)	MBR20060CT (R)	MBR20080CT (R)	MBR200100CT (R)	Unit
Diode forward voltage	V_F	$I_F = 100 \text{ A}$, $T_J = 25 \text{ }^\circ\text{C}$	0.65	0.75	0.84	0.84	V
Reverse current	I_R	$V_R = 20 \text{ V}$, $T_J = 25 \text{ }^\circ\text{C}$	5	5	5	5	mA
		$V_R = 20 \text{ V}$, $T_J = 125 \text{ }^\circ\text{C}$	200	200	200	200	

Thermal characteristics

Thermal resistance, junction - case	$R_{\theta JC}$		0.5	0.5	0.5	0.5	$^\circ\text{C/W}$
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Figure 1- Typical Forward Characteristics

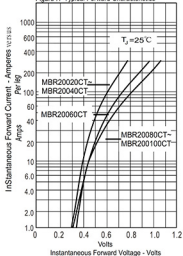


Figure 2- Forward Derating Curve

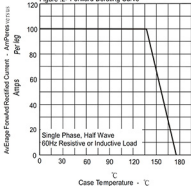


Figure 3- Peak Forward Surge Current

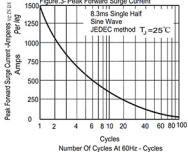


Figure 4- Typical Reverse Characteristics

